

NSVT1418L

Bipolar Transistor -160 V, -1 A, Low $V_{CE(sat)}$, PNP Single

This device is bipolar junction transistor featuring high current, low saturation voltage, and high speed switching.

Suitable for automotive applications. AEC-Q101 qualified and PPAP capable.

Features

- Large Current Capacitance
- Low Collector to Emitter Saturation Voltage
- High Speed Switching
- High Allowable Power Dissipation
- AEC-Q101 Qualified and PPAP Capable
- Pb-Free, Halogen Free and RoHS Compliant
- Ultra Small Package Facilitates Miniaturization in End Products

Typical Applications

- High Side Switch
- Lighting, Infotainment

ABSOLUTE MAXIMUM RATINGS at $T_A = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Collector to Base Voltage	V_{CBO}	-180	V
Collector to Emitter Voltage	V_{CEO}	-160	V
Emitter to Base Voltage	V_{EBO}	-6	V
Collector Current	I_C	-1	A
Collector Current (Pulse)	I_{CP}	-2	A
Collector Dissipation (Note 1)	P_C	0.42	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface mounted on ceramic substrate. (250 mm² x 0.8 mm)



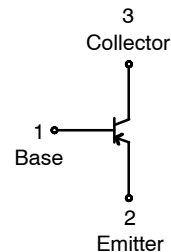
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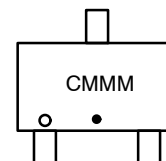


SOT-23
CASE 318-08

ELECTRICAL CONNECTION



MARKING DIAGRAM



CMM = Specific Device Code
M = Single Digit Date Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Collector Cutoff Current	I_{CBO}	$V_{CB} = -120\text{ V}, I_E = 0\text{ A}$			-0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = -4\text{ V}, I_C = 0\text{ A}$			-0.1	μA
DC Current Gain	h_{FE1}	$V_{CE} = -5\text{ V}, I_C = -100\text{ mA}$	100		400	
	h_{FE2}	$V_{CE} = -5\text{ V}, I_C = -10\text{ mA}$	90			
Gain-Bandwidth Product	f_T	$V_{CE} = -10\text{ V}, I_C = -50\text{ mA}$		120		MHz
Output Capacitance	C_{ob}	$V_{CB} = -10\text{ V}, f = 1\text{ MHz}$		11		pF
Collector to Emitter Saturation Voltage	$V_{CE(sat)1}$	$I_C = -250\text{ mA}, I_B = -25\text{ mA}$		-0.1	-0.5	V
	$V_{CE(sat)2}$	$I_C = -250\text{ mA}, I_B = -50\text{ mA}$		-0.08	-0.13	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -250\text{ mA}, I_B = -25\text{ mA}$		-0.8	-1.2	V
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -10\text{ }\mu\text{A}, I_E = 0\text{ A}$	-180			V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1\text{ mA}, R_{BE} = \infty$	-160			V
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10\text{ }\mu\text{A}, I_C = 0\text{ A}$	-6			V
Turn-On Time	t_{on}	See Figure 1		90		ns
Storage Time	t_{stg}			1000		ns
Fall Time	t_f			70		ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

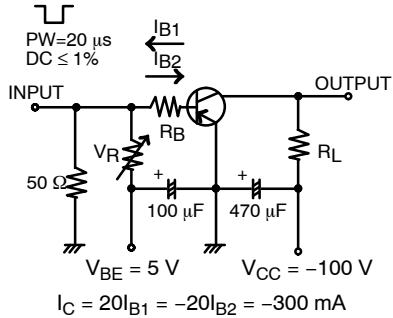


Figure 1. Switching Time Test Circuit

TYPICAL CHARACTERISTICS

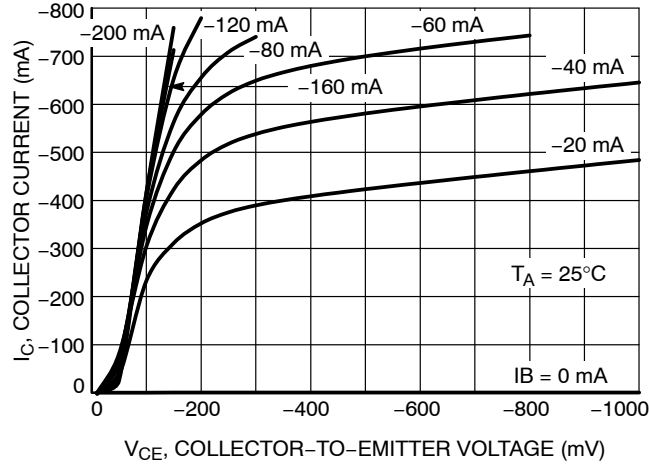


Figure 2. I_C vs. V_{CE}

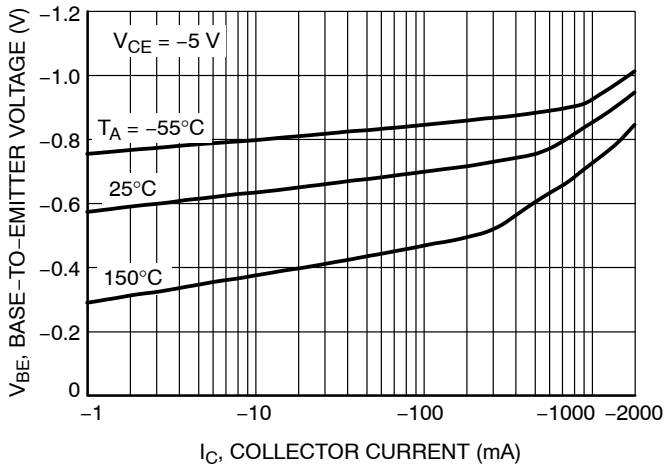


Figure 3. V_{BE} vs. I_C

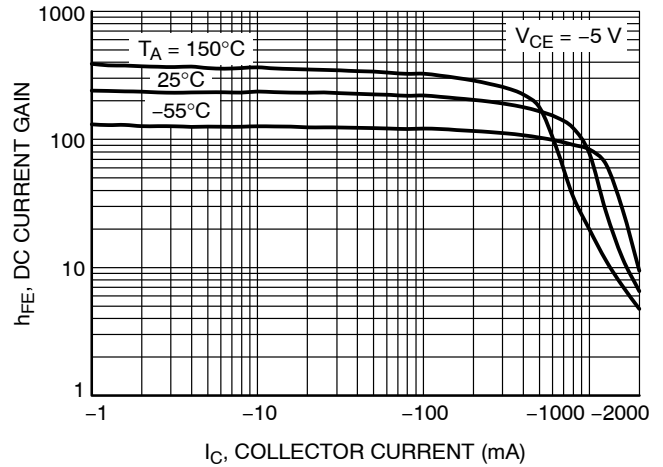


Figure 4. h_{FE} vs. I_C

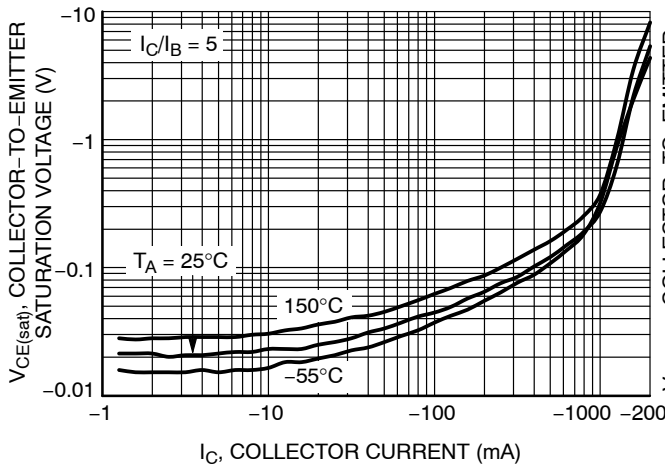


Figure 5. $V_{CE(sat)}$ vs. I_C

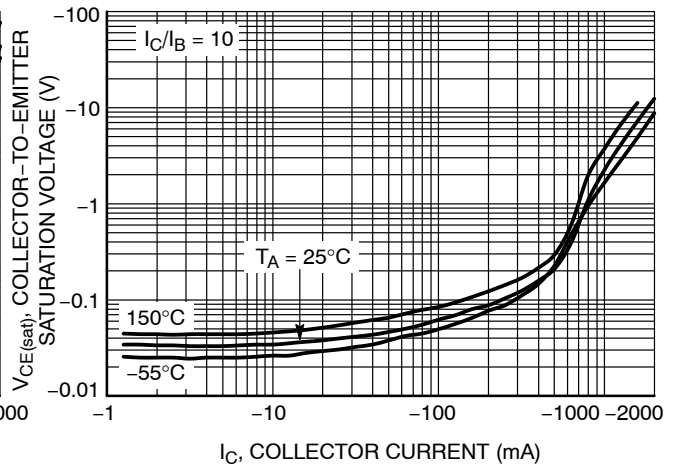


Figure 6. $V_{CE(sat)}$ vs. I_C

TYPICAL CHARACTERISTICS

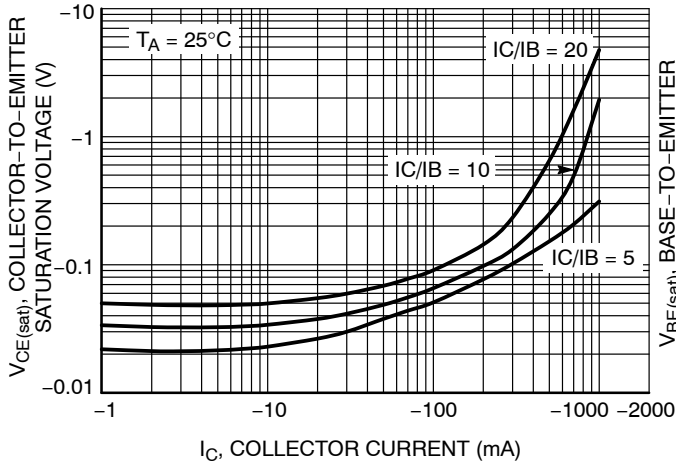


Figure 7. $V_{CE(sat)}$ vs. I_C

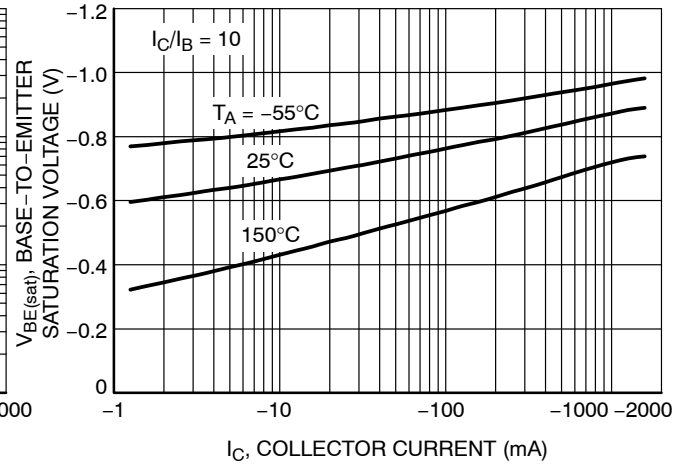


Figure 8. $V_{BE(sat)}$ vs. I_C

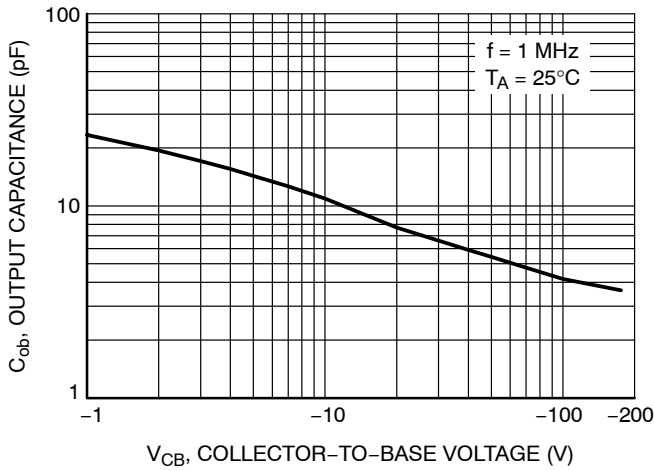


Figure 9. C_{ob} vs. V_{CB}

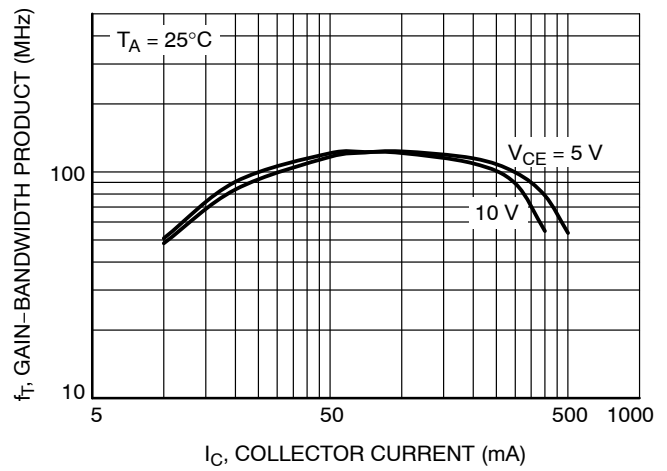


Figure 10. f_T vs. I_C

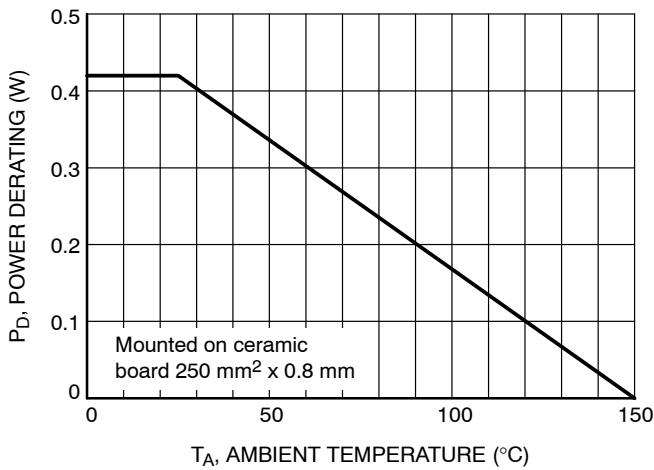


Figure 11. Power Derating

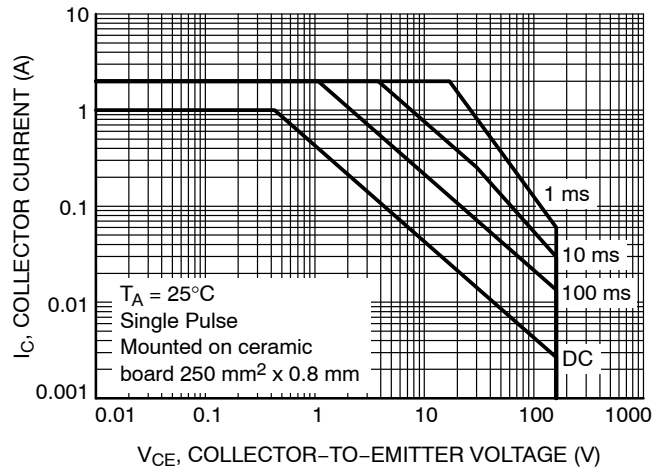


Figure 12. Safe Operating Area

NSVT1418L

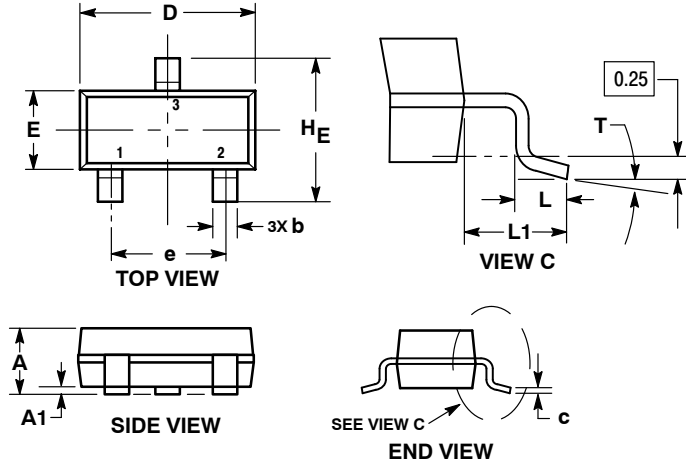
ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing) †
NSVT1418LT1G	CMM	SOT-23 (Pb-Free / Halogen Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 ISSUE AS

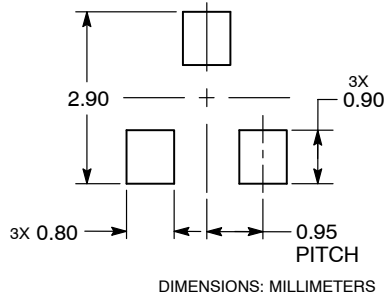


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
He	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

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